

isc N-Channel MOSFET Transistor

IRF823

FEATURES

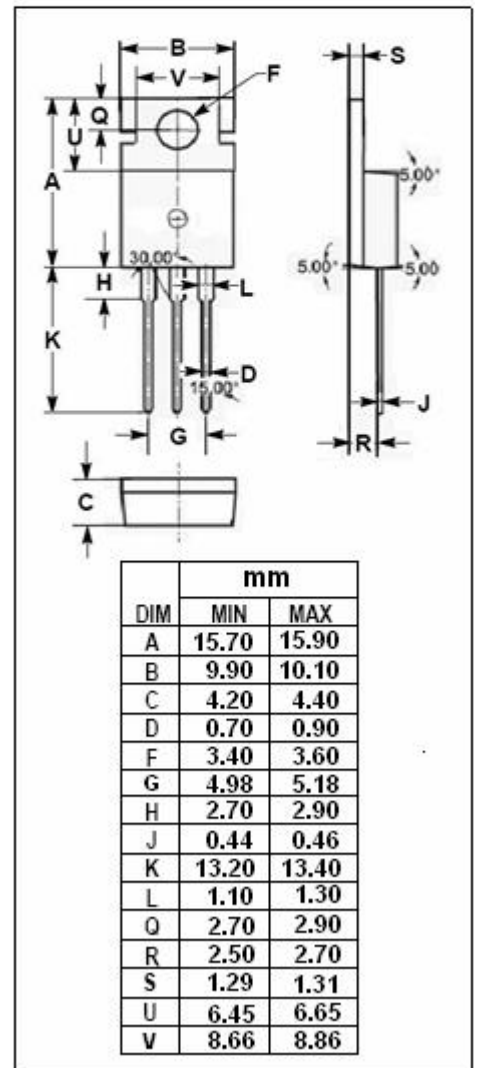
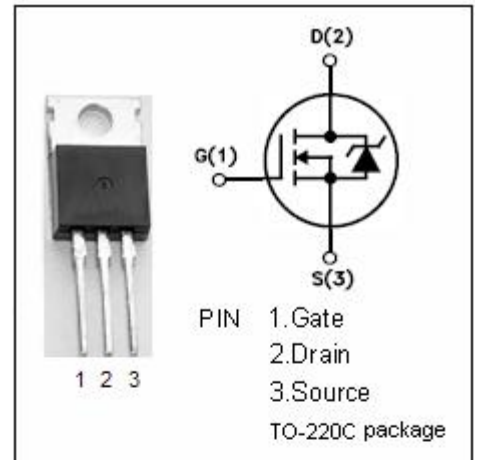
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Rugged Gate Oxide Technology

DESCRIPTION

- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	450	V
V _{GS}	Gate-Source Voltage-Continuous	±20	V
I _D	Drain Current-Continuous	2.0	A
I _{DM}	Drain Current-Single Pluse	7	A
P _D	Total Dissipation @T _C =25°C	50	W
T _J	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.5	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	80	°C/W

isc N-Channel MOSFET Transistor**IRF823****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=0.25\text{mA}$	450		V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25\text{mA}$	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=1.4\text{A}$		4	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$		± 500	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=450\text{V}; V_{GS}=0$		250	μA
V_{SD}	Forward On-Voltage	$I_S=2.5\text{A}; V_{GS}=0$		1.6	V
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, F=1.0\text{MHz}$		510	pF
C_{oss}	Output Capacitance			60	pF
C_{rss}	Reverse Transfer Capacitance			26	pF

• SWITCHING CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$T_d(on)$	Turn-on Delay Time	$V_{DD}=250\text{V}, I_D=2.5\text{A}$ $R_G=18\Omega$		11	15	ns
T_r	Rise Time			11	18	ns
$T_d(off)$	Turn-off Delay Time			29	42	ns
T_f	Fall Time			12	18	ns